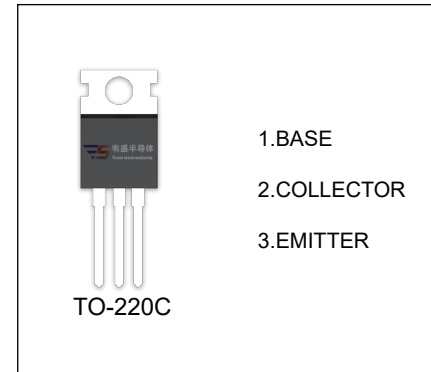


## 2SA940 TRANSISTOR (PNP)

### FEATURES

- Wide Safe Operating Area.
- Complementary to 2SC2703



### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-150	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-1.5	A
$P_C$	Collector Power Dissipation	1.5	W
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -120\text{V}, I_E = 0$			-10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-10	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -0.5\text{A}, I_B = -50\text{mA}$			-1.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}$	-0.65		-0.85	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}$		4		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		55		pF